

NPN SILICON MICROWAVE TRANSISTOR

DESCRIPTION:

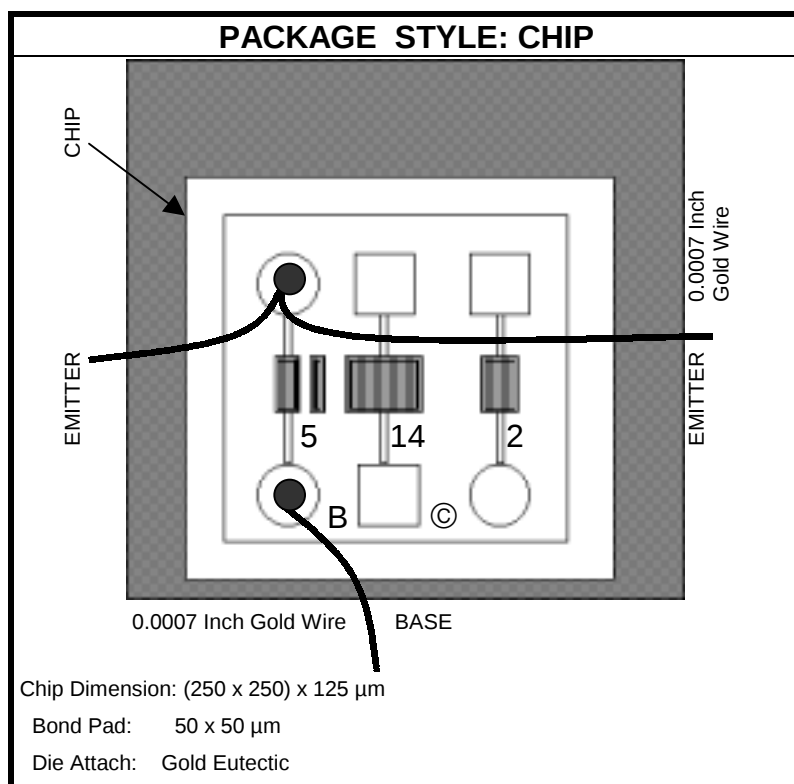
The **ASI NE64700** is a bipolar transistor Designed for low noise applications at VHF, UHF and microwave frequencies up to 12 GHz.

FEATURES:

- $P_G = 18.1$ dB Typical @ 1.0 GHz
- $NF = 1.6$ dB Typical @ 1.0 GHz

MAXIMUM RATINGS

I_C	20 mA
V_{CEO}	7.0 V
V_{CBO}	9.0 V
V_{EBO}	1.5 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 8.0$ V					0.2	μ A
I_{EBO}	$V_{EB} = 1.0$ V					1.0	μ A
h_{FE}	$V_{CE} = 8.0$ V	$I_C = 10$ mA		50	100	250	---
C_{CB}	$V_{CB} = 8.0$ V		$f = 1.0$ MHz		0.11		pF
NF	$V_{CE} = 8.0$ V	$I_C = 2.0$ mA	$f = 1.0$ MHz		1.6		dB
P_G	$V_{CE} = 8.0$ V	$I_C = 10$ mA	$f = 1.0$ GHz		15		dB
P_{1dB}					12		dBm
f_t	$I_C = 10$ mA				12		GHz
$ S_{21} $	$V_{CE} = 8.0$ V	$I_C = 10$ mA	$f = 1.0$ GHz		7.5		dB
		$I_C = 20$ mA	$f = 1.0$ GHz		18.1		
		$I_C = 10$ mA	$f = 2.0$ GHz		12.8		
		$I_C = 20$ mA	$f = 2.0$ GHz		12.6		